



ZVP3310F

SOT23 P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max
-100V	20Ω @ V _{GS} = -10V	-75mA

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Load Switching

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>ZVP3310FQ</u>)

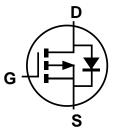
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (63)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

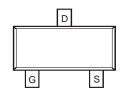
SOT23



Top View



Internal Schematic



Top View

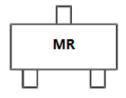
Ordering Information (Note 4)

Part Number	Case	Packaging
ZVP3310FTA	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



MR = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	-100	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	Steady State	I _D	-75	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	-1.2	Α
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	-1.2	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (@T _A = +25°C)	P _D	330	mW
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

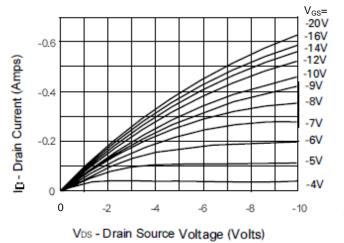
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

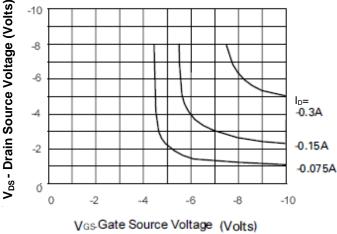
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)	<u> </u>		-				
Drain-Source Breakdown Voltage	BV _{DSS}	-100	_	_	V	$V_{GS} = 0V$, $I_D = -1mA$	
		_	_	-1	μA	V _{DS} = -100V, V _{GS} = 0V	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-50	μA	V _{DS} = -80V, V _{GS} = 0V, T = +125°C	
Gate-Source Leakage	I _{GSS}	_	_	±20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)						•	
Gate Threshold Voltage	V _{GS(TH)}	-1.5	_	-3.5	V	$V_{DS} = V_{GS}$, $I_D = -1mA$	
Static Drain-Source On-Resistance (Note 5)	R _{DS(ON)}	_	_	20	Ω	$V_{GS} = -10V, I_D = -150mA$	
On-State Drain Current (Note 5)	I _{D(ON)}	-300	_	_	mA	$V_{DS} = -25V, V_{GS} = -10V$	
Forward Transconductance (Note 5)	gfs	50	_	_	mS	$V_{DS} = -25V, I_{D} = -150mA$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	_	_	50		$V_{DS} = -25V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	_	_	15	pF		
Reverse Transfer Capacitance	C _{rss}	_	_	5			
Turn-On Delay Time	t _{D(ON)}	_	_	8		V _{DD} = -25V, I _D = -150mA	
Turn-On Rise Time	t _R	_	_	8	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	_	8	1115		
Turn-Off Fall Time	t _F	_		8			

Notes:

- 5. Measured under pulsed conditions. Width = 300ms. Duty cycle <=2%.6. Short duration pulse test used to minimize self-heating effect.
- 7. Guaranteed by design. Not subject to product testing.



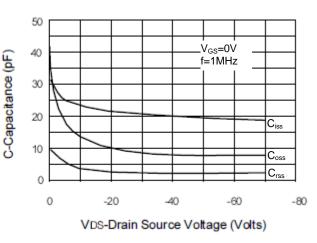




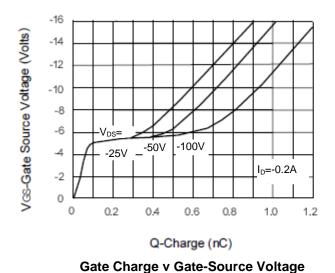
Saturation Characteristics

100 90 gfs-Transconductance (mS) V_{DS}=-10V 80 70 60 50 40 30 20 10 0 -0.1 -0.2 -0.3 -0.4 -0.5 -0.6 -0.7 -0.8 ID- Drain Current (Amps)

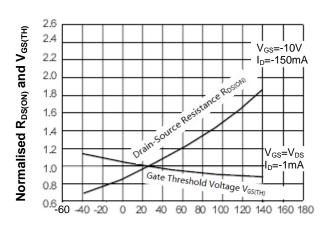
Voltage Saturation Characteristics



Transconductance v Drain Current



Capacitance v Drain-Source Voltage



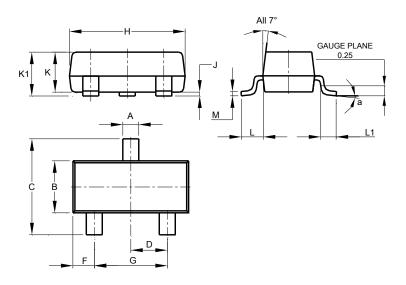
 $$T_{J}$$ - Junction Temperature (°C) Normalised $R_{DS(ON)}$ and $V_{GS(TH)}$ v Temperature



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

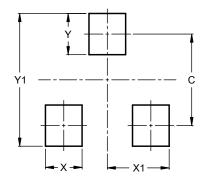


SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	0°	8°			
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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